

# Standard Rectifier Module

$$V_{RRM} = 2 \times 1600 \text{ V}$$

$$I_{FAV} = 210 \text{ A}$$

$$V_F = 1.04 \text{ V}$$


Phase leg

Part number

**MDMA210P1600YD**



Backside: isolated

 E72873



## Features / Advantages:

- Package with DCB ceramic
- Improved temperature and power cycling
- Planar passivated chips
- Very low forward voltage drop
- Very low leakage current

## Applications:

- Diode for main rectification
- For single and three phase bridge configurations
- Supplies for DC power equipment
- Input rectifiers for PWM inverter
- Battery DC power supplies
- Field supply for DC motors

## Package: Y4

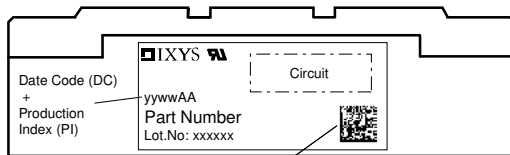
- Isolation Voltage: 4800 V~
- Industry standard outline
- RoHS compliant
- Height: 30 mm
- Base plate: DCB ceramic
- Reduced weight
- Advanced power cycling

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Rectifier				Ratings			
Symbol	Definition	Conditions		min.	typ.	max.	Unit
$V_{RSM}$	max. non-repetitive reverse blocking voltage			$T_{VJ} = 25^{\circ}C$		1700	V
$V_{RRM}$	max. repetitive reverse blocking voltage			$T_{VJ} = 25^{\circ}C$		1600	V
$I_R$	reverse current	$V_R = 1600$ V		$T_{VJ} = 25^{\circ}C$		1	mA
		$V_R = 1600$ V		$T_{VJ} = 150^{\circ}C$		15	mA
$V_F$	forward voltage drop	$I_F = 210$ A		$T_{VJ} = 25^{\circ}C$		1.13	V
		$I_F = 420$ A				1.34	V
		$I_F = 210$ A		$T_{VJ} = 125^{\circ}C$		1.04	V
		$I_F = 420$ A				1.30	V
$I_{FAV}$	average forward current	$T_C = 100^{\circ}C$		$T_{VJ} = 150^{\circ}C$		210	A
		rectangular	d = 0.5				
$V_{FO}$	threshold voltage			$T_{VJ} = 150^{\circ}C$		0.76	V
$r_F$	slope resistance					1.2	mΩ
						} for power loss calculation only	
$R_{thJC}$	thermal resistance junction to case					0.17	K/W
$R_{thCH}$	thermal resistance case to heatsink				0.09		K/W
$P_{tot}$	total power dissipation			$T_C = 25^{\circ}C$		735	W
$I_{FSM}$	max. forward surge current	t = 10 ms; (50 Hz), sine		$T_{VJ} = 45^{\circ}C$		6.60	kA
		t = 8,3 ms; (60 Hz), sine		$V_R = 0$ V		7.13	kA
		t = 10 ms; (50 Hz), sine		$T_{VJ} = 150^{\circ}C$		5.61	kA
		t = 8,3 ms; (60 Hz), sine		$V_R = 0$ V		6.06	kA
$I^2t$	value for fusing	t = 10 ms; (50 Hz), sine		$T_{VJ} = 45^{\circ}C$		217.8	kA <sup>2</sup> s
		t = 8,3 ms; (60 Hz), sine		$V_R = 0$ V		211.5	kA <sup>2</sup> s
		t = 10 ms; (50 Hz), sine		$T_{VJ} = 150^{\circ}C$		157.4	kA <sup>2</sup> s
		t = 8,3 ms; (60 Hz), sine		$V_R = 0$ V		152.8	kA <sup>2</sup> s
$C_J$	junction capacitance	$V_R = 400$ V; f = 1 MHz		$T_{VJ} = 25^{\circ}C$		208	pF

Package Y4				Ratings			
Symbol	Definition	Conditions	min.	typ.	max.	Unit	
$I_{RMS}$	RMS current	per terminal			300	A	
$T_{VJ}$	virtual junction temperature		-40		150	°C	
$T_{op}$	operation temperature		-40		125	°C	
$T_{stg}$	storage temperature		-40		125	°C	
<b>Weight</b>					150	g	
$M_D$	mounting torque		2.25		2.75	Nm	
$M_T$	terminal torque		4.5		5.5	Nm	
$d_{Spp/App}$	creepage distance on surface   striking distance through air	terminal to terminal	14.0	10.0		mm	
$d_{Spb/Apb}$		terminal to backside	16.0	16.0		mm	
$V_{ISOL}$	isolation voltage	t = 1 second		4800		V	
		t = 1 minute	50/60 Hz, RMS; $I_{ISOL} \leq 1$ mA	4000		V	



Data Matrix: part no. (1-19), DC + PI (20-25), lot.no.# (26-31), blank (32), serial no.# (33-36)

### Part description

M = Module  
 D = Diode  
 M = Standard Rectifier  
 A = (up to 1800V)  
 210 = Current Rating [A]  
 P = Phase leg  
 1600 = Reverse Voltage [V]  
 YD = Y4-M6

Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	MDMA210P1600YD	MDMA210P1600YD	Box	6	517762

Similar Part	Package	Voltage class
MDMA180P1600YD	Y4-M6	1600
MDMA280P1600YD	Y4-M6	1600

### Equivalent Circuits for Simulation

\* on die level

$T_{VJ} = 150^{\circ}\text{C}$



Rectifier

$V_{0\ max}$	threshold voltage	0.76	V
$R_{0\ max}$	slope resistance *	0.57	mΩ



**Outlines Y4**



Dim.	MIN [mm]	MAX [mm]	MIN [inch]	MAX [inch]
a	30.0	30.6	1.181	1.205
b	typ. 0.25		typ. 0.010	
c	64.0	65.0	2.520	2.559
d	6.5	7.0	0.256	0.275
e	4.9	5.1	0.193	0.201
h	93.5	94.5	3.681	3.720
i	79.5	80.5	3.130	3.169
k	33.4	34.0	1.315	1.339
l	16.7	17.3	0.657	0.681
m	22.7	23.3	0.894	0.917
n	22.7	23.3	0.894	0.917
o	14.0	15.0	0.551	0.591
p	typ. 10.5		typ. 0.413	



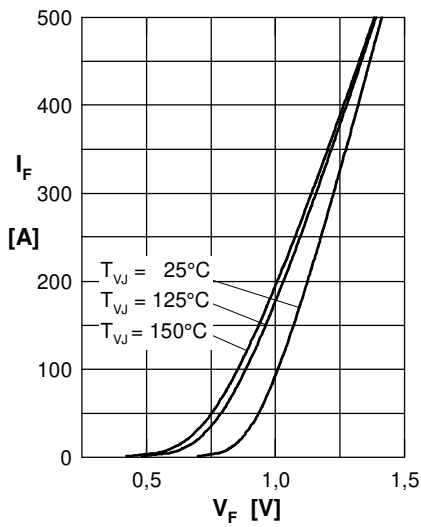
**Rectifier**


Fig. 1 Forward current versus voltage drop per diode

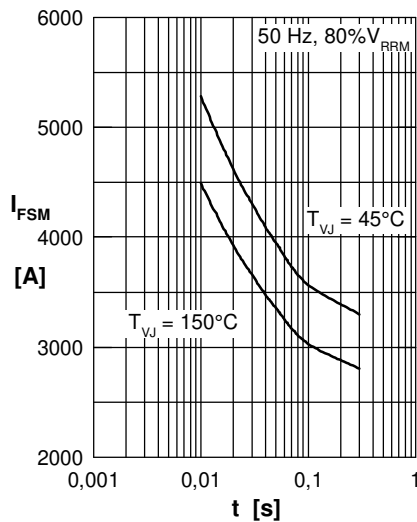


Fig. 2 Surge overload current vs. time per diode

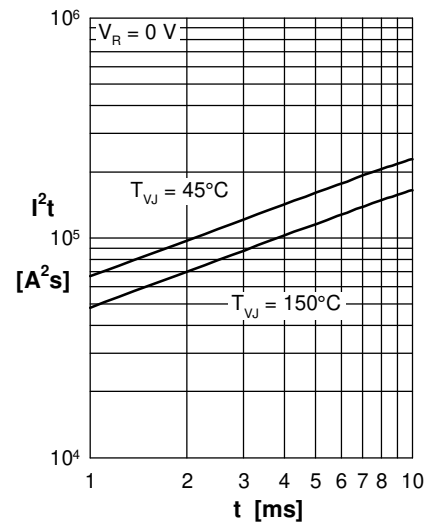
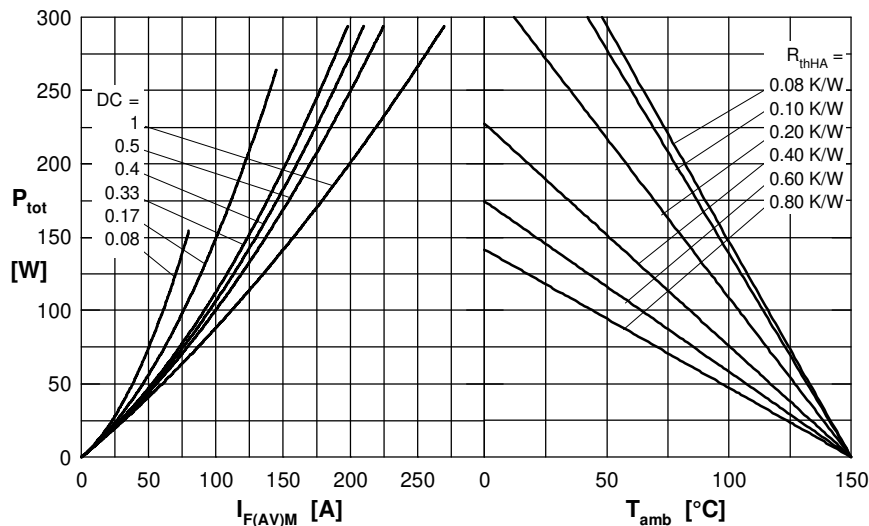

 Fig. 3  $I^2t$  versus time per diode


Fig. 4 Power dissipation vs. forward current and ambient temperature per diode

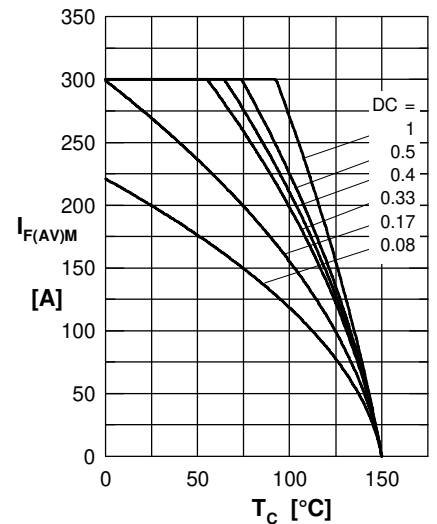


Fig. 5 Max. forward current vs. case temperature per diode

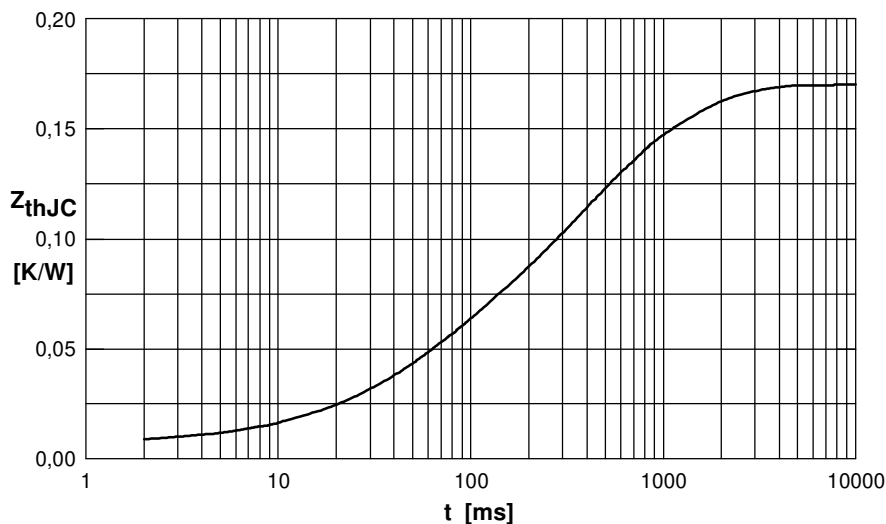


Fig. 6 Transient thermal impedance junction to case vs. time per diode

 Constants for  $Z_{thJC}$  calculation:

i	$R_{thi}$ (K/W)	$t_i$ (s)
1	0.007	0.0005
2	0.036	0.0500
3	0.072	0.3000
4	0.055	1.0000